

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:
Please rewrite claim 7 as follows.

Listing of Claims:

Claims 1-6: (cancelled)

7. (currently amended) An apparatus for fabricating a Group III-V nitride film by a MOCVD method, comprising:

a reactor in which a MOCVD reaction between a Group III raw material gas and a Group V material gas is generated;

a susceptor to hold a substrate thereon installed in the reactor, the susceptor includes a groove portion and the substrate is positioned in the groove portion; and

a heater to heat the substrate to a predetermined temperature via the susceptor,
wherein

at least one of an interior wall of the reactor and the susceptor is coated with an $\text{Al}_a\text{Ga}_b\text{In}_c\text{N}$ ($a+b+c=1$, $a>0$) film, which is heated to a temperature of 1000°C or more.

8. (previously presented) An apparatus as defined in claim 7, wherein the $\text{Al}_a\text{Ga}_b\text{In}_c\text{N}$ ($a+b+c=1$, $a>0$) film includes at least 50 atomic percent of Al ($a>0.5$) with respect to all of the Group III elements of the Periodic Table that are present in the film.

9. (previously presented) An apparatus as defined in claim 8, wherein the $\text{Al}_a\text{Ga}_b\text{In}_c\text{N}$ ($a+b+c=1$, $a>0$) film is an AlN film.

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